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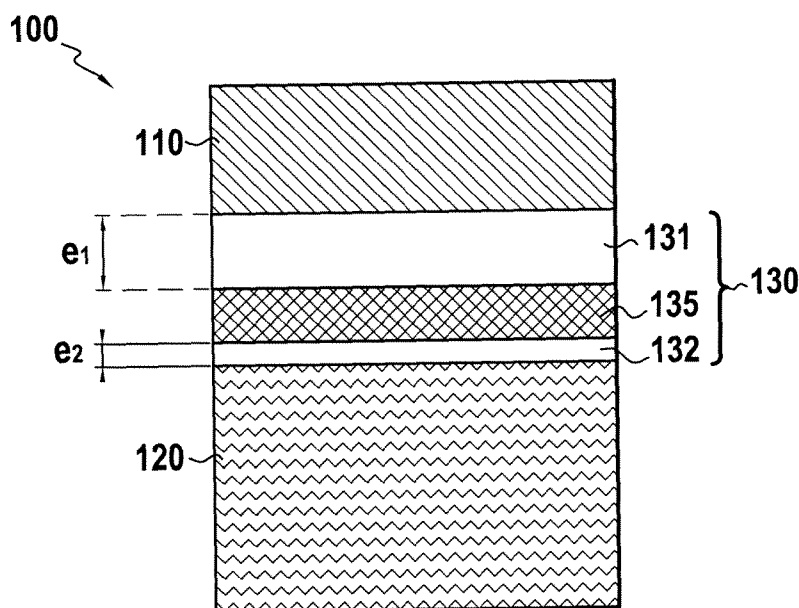
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(54) Title: A MAGNETORESISTIVE TUNNEL JUNCTION MAGNETIC DEVICE AND ITS APPLICATION TO MRAM



(57) Abstract: The magnetic device comprises a magnetic device comprising a magnetoresistive tunnel junction (100), itself comprising: a reference magnetic layer (120) having magnetization in a direction that is fixed; a storage magnetic layer (110) having magnetization in a direction that is variable; and an intermediate layer (130) acting as a tunnel barrier that is essentially semiconductor or electrically insulating and that separates the reference magnetic layer (120) from the storage magnetic layer (110). The potential profile of the intermediate layer (130) is asymmetrical across the thickness of said layer (130) so as to produce a current response that is asymmetrical as a function of the applied voltage. The device is applicable to magnetic random access memories.